



SOT-523 Plastic-Encapsulate Diode

DAN222

SWITCHING DIODE

FEATURES:

Power dissipation

 P_D : 150 mW ($T_{amb}=25^{\circ}C$)

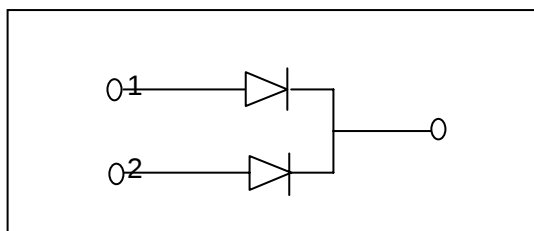
Collector current

 I_F : 100 mA

Collector-base voltage

 V_R : 80 V

Operating and storage junction temperature range

 T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$ **SOT-523****CIRCUIT:**

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MARKING: N**ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	80		V
Reverse voltage leakage current	I_R	$V_R=70V$		0.1	μA
Forward voltage	V_F	$I_F=100mA$		1.2	V
Diode capacitance	C_D	$V_R=6V, f=1MHz$		3.5	pF
Reverse recovery time	t_{rr}	$V_R=6V, I_F=5mA$		4	ns